

PJ
temperature at or slightly below a thin-film glass transition temperature of said metal containing resistance variable material.

PB
35. (Amended) The element of claim 34 wherein said glass has a germanium molar concentration number greater than about 0.23.

36. (Amended) The element of claim 34 wherein said glass has a mean coordination number of at least about 2.46.

PY
40. (Amended) The element of claim 39 wherein said metal is silver.

41. (Amended) The element of claim 39 wherein said annealed metal containing resistance variable material comprises a germanium-selenide glass.

42. (Amended) The element of claim 41 wherein said germanium-selenide glass has a germanium molar concentration number of greater than about 0.23.

43. (Amended) The element of claim 39 wherein said annealed metal containing resistance variable material has a mean coordination number of at least about 2.46.

44. (Amended) The element of claim 39 wherein said annealed metal containing resistance variable material comprises a silver doped germanium-selenide.

AS
46. (Amended) The element of claim 45 wherein said metal comprises silver.

47. (Amended) The element of claim 45 wherein said annealed metal containing resistance variable material comprises a germanium-selenide glass.

AS
48. (Amended) The element of claim 47 wherein said germanium-selenide glass has a germanium molar concentration number of greater than about 0.23.

49. (Amended) The element of claim 45 wherein said annealed metal containing resistance variable material has a mean coordination number of at least about 2.46.

50. (Amended) The element of claim 45 wherein said annealed metal containing resistance variable material comprises a silver doped germanium-selenide.

51. (Amended) A computer device having a memory, said memory comprising:
AS
an annealed metal containing resistance variable material having increased rigidity.

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58. (Amended) The element of claim 57 wherein said annealed resistance variable material comprises silver.

59. (Amended) The element of claim 57 wherein said annealed resistance variable material comprises a germanium-selenide glass.